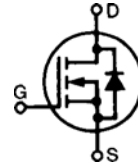


# HiPerFET™ Power MOSFETs Q-Class

**IXFH 6N100Q**  
**IXFT 6N100Q**

**V<sub>DSS</sub> = 1000 V**  
**I<sub>D25</sub> = 6 A**  
**R<sub>DS(on)</sub> = 1.9 Ω**

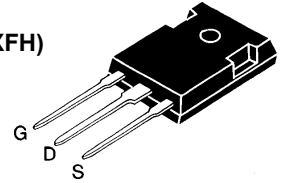
N-Channel Enhancement Mode  
Avalanche Rated, Low Q<sub>g</sub>, High dv/dt



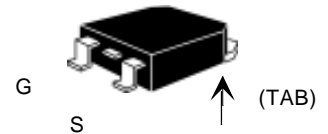
**t<sub>rr</sub> ≤ 250 ns**

Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	1000	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C; R <sub>GS</sub> = 1 MΩ	1000	V
V <sub>GS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	6	A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	24	A
I <sub>AR</sub>	T <sub>C</sub> = 25°C	6	A
E <sub>AR</sub>	T <sub>C</sub> = 25°C	20	mJ
E <sub>AS</sub>		700	mJ
dv/dt	I <sub>S</sub> ≤ I <sub>DM</sub> , di/dt ≤ 100 A/μs, V <sub>DD</sub> ≤ V <sub>DSS</sub> , T <sub>J</sub> ≤ 150°C, R <sub>G</sub> = 2 Ω	5	V/ns
P <sub>D</sub>	T <sub>C</sub> = 25°C	180	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
T <sub>L</sub>	1.6 mm (0.063 in) from case for 10 s	300	°C
M <sub>d</sub>	Mounting torque	1.13/10	Nm/lb.in.
Weight	TO-247	6	g
	TO-268	4	g

**TO-247 AD (IXFH)**



**TO-268 (D3) (IXFT)**



G = Gate      D = Drain  
S = Source      TAB = Drain

Symbol	Test Conditions	Characteristic Values (T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
V <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 1 mA	1000		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 2.5 mA	2.0		4.5 V
I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V <sub>DC</sub> , V <sub>DS</sub> = 0			±100 nA
I <sub>DSS</sub>	V <sub>DS</sub> = 0.8 V <sub>DSS</sub> V <sub>GS</sub> = 0 V			T <sub>J</sub> = 25°C 50 μA
				T <sub>J</sub> = 125°C 1 mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 I <sub>D25</sub> Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %			1.9 Ω

## Features

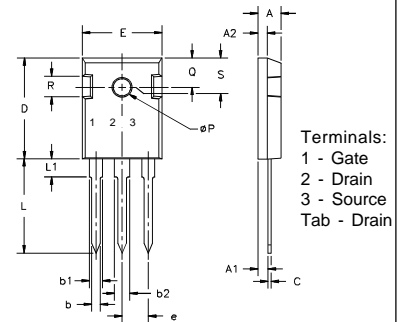
- IXYS advanced low Q<sub>g</sub> process
- Low gate charge and capacitances  
- easier to drive  
- faster switching
- International standard packages
- Low R<sub>DS(on)</sub>
- Unclamped Inductive Switching (UIS) rated
- Molding epoxies meet UL 94 V-0 flammability classification

## Advantages

- Easy to mount
- Space savings
- High power density

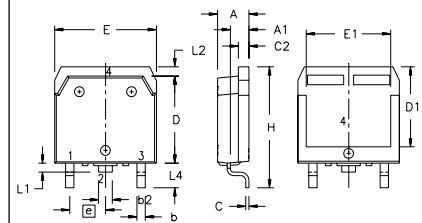
Symbol	Test Conditions	Characteristic Values ( $T_j = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$ , pulse test	3	5	S
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		2200	pF
$C_{oss}$			180	pF
$C_{rss}$			30	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 4.7\ \Omega$ (External),		10	ns
$t_r$			15	ns
$t_{d(off)}$			22	ns
$t_f$			12	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		48	nC
$Q_{gs}$			17	nC
$Q_{gd}$			22	nC
$R_{thJC}$			0.7	K/W
$R_{thCK}$	(TO-247)		0.25	K/W

Symbol	Test Conditions	Characteristic Values ( $T_j = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$I_s$	$V_{GS} = 0\text{ V}$			9 A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$			24 A
$V_{SD}$	$I_F = I_s, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = I_s, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		0.75	250 ns
$Q_{RM}$			7.5	$\mu\text{C}$
$I_{RM}$				A

**TO-247 AD (IXFH) Outline**


Terminals:  
1 - Gate  
2 - Drain  
3 - Source  
Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.087	.102
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

**TO-268 Outline**


Terminals: 1 - Gate 2 - Drain  
3 - Source Tab - Drain

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	54.3	55.1	13.80	14.00
D1	48.8	50.0	12.40	12.70
E	62.4	63.2	15.85	16.05
E1	52.4	53.5	13.30	13.60
e	.215	BSC	5.45	BSC
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010	BSC	0.25	BSC
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715  
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025